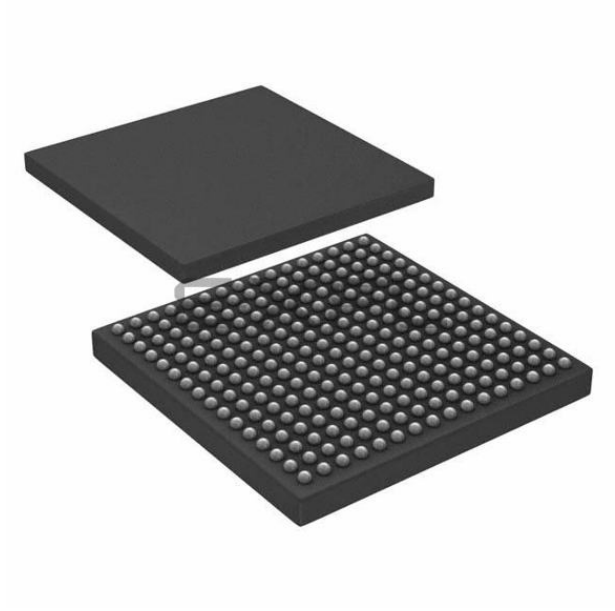

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	256KB
RAM Size	64KB
Peripherals	DMA, POR, WDT
Connectivity	EBI/EMI, Ethernet, I²C, SPI, UART/USART
Speed	100MHz
Primary Attributes	ProASIC®3 FPGA, 200K Gates, 4608 D-Flip-Flops
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a2f200m3f-1fg256

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in the Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs/CCCs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- The number of eNVM blocks used in the design
- The analog block used in the design, including the temperature monitor, current monitor, ABPS, sigma-delta DAC, comparator, low power crystal oscillator, RC oscillator and the main crystal oscillator
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-17 on page 2-18.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-18 on page 2-18.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-18 on page 2-18.
- Read rate to the eNVM blocks

The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

SoC Mode, Standby Mode, and Time Keeping Mode.

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

SoC Mode

$P_{STAT} = P_{DC1} + (N_{INPUTS} * P_{DC7}) + (N_{OUTPUTS} * P_{DC8}) + (N_{PLLS} * P_{DC9})$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

N_{PLLS} is the number of PLLs available in the device.

Standby Mode

$P_{STAT} = P_{DC2}$

Time Keeping Mode

$P_{STAT} = P_{DC3}$

Total Dynamic Power Consumption—P_{DYN}

SoC Mode

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL} + P_{eNVM} + P_{XTL\text{-}OSC} + P_{RC\text{-}OSC} + P_{AB} + P_{LPXTAL\text{-}OSC} + P_{MSS}$

Standby Mode

$P_{DYN} = P_{RC\text{-}OSC} + P_{LPXTAL\text{-}OSC}$

Time Keeping Mode

$P_{DYN} = P_{LPXTAL\text{-}OSC}$

Global Clock Dynamic Contribution—P_{CLOCK}

SoC Mode

$P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * PAC3 + N_{S\text{-}CELL} * P_{AC4}) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Device Architecture" chapter of the *SmartFusion FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Device Architecture" chapter of the *SmartFusion FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

Standby Mode and Time Keeping Mode

$P_{CLOCK} = 0$ W

Sequential Cells Dynamic Contribution—$P_{S\text{-}CELL}$

SoC Mode

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (P_{AC5} + (\alpha_1 / 2) * P_{AC6}) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-17 on page 2-18.

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

$P_{S\text{-}CELL} = 0$ W

Combinatorial Cells Dynamic Contribution—$P_{C\text{-}CELL}$

SoC Mode

$P_{C\text{-}CELL} = N_{C\text{-}CELL} * (\alpha_1 / 2) * P_{AC7} * F_{CLK}$

$N_{C\text{-}CELL}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-17 on page 2-18.

F_{CLK} is the global clock signal frequency.

Standby Mode and Time Keeping Mode

$P_{C\text{-}CELL} = 0$ W

Routing Net Dynamic Contribution—P_{NET}

SoC Mode

$P_{NET} = (N_{S\text{-}CELL} + N_{C\text{-}CELL}) * (\alpha_1 / 2) * P_{AC8} * F_{CLK}$

$N_{S\text{-}CELL}$ is the number VersaTiles used as sequential modules in the design.

$N_{C\text{-}CELL}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-17 on page 2-18.

F_{CLK} is the frequency of the clock driving the logic including these nets.

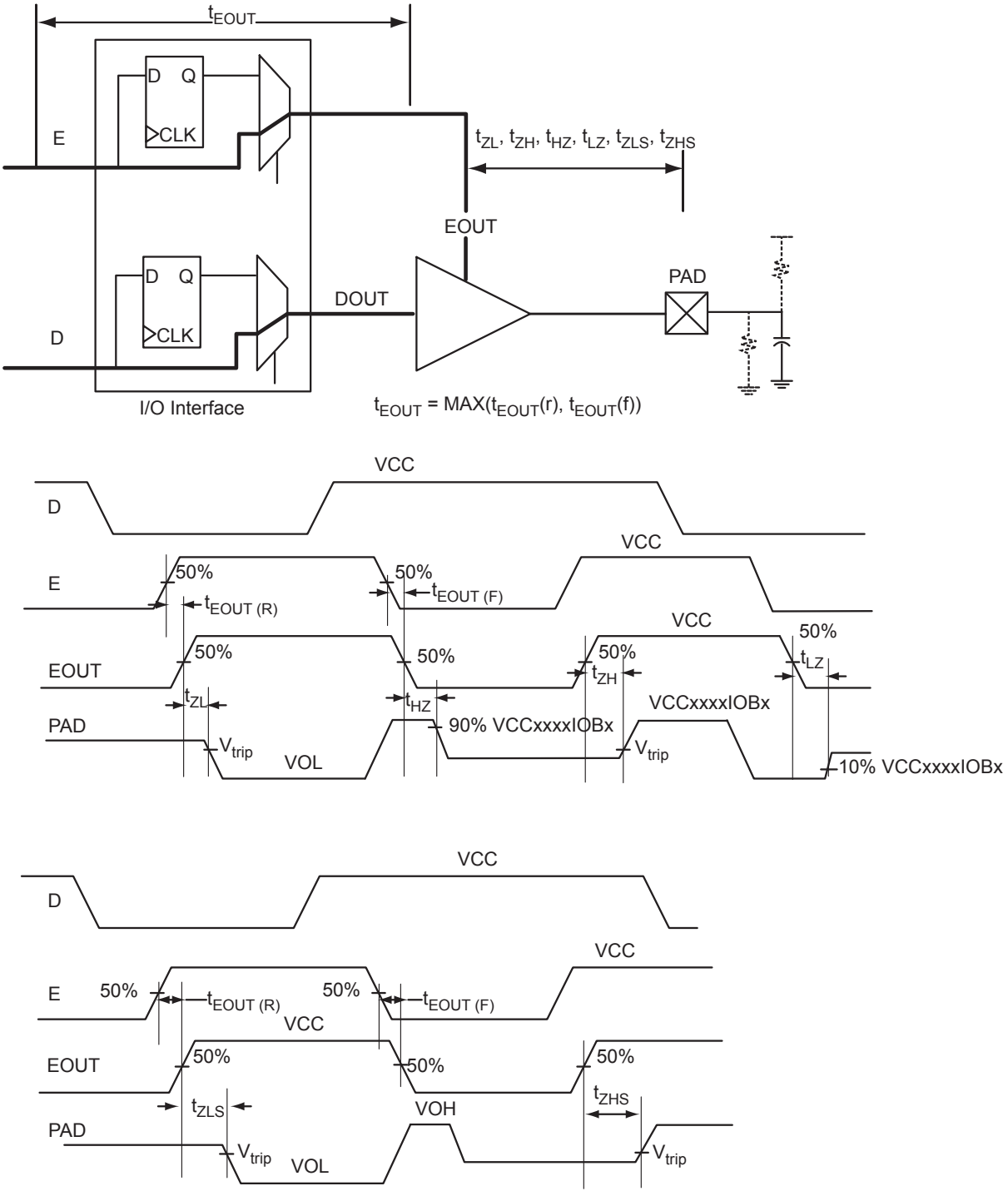

Figure 2-5 • **Tristate Output Buffer Timing Model and Delays (example)**

Detailed I/O DC Characteristics

***Table 2-26* • Input Capacitance**

Symbol	Definition	Conditions	Min.	Max.	Units
C_{IN}	Input capacitance	V_{IN} = 0, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on the clock pin	V_{IN} = 0, f = 1.0 MHz		8	pF

***Table 2-27* • I/O Output Buffer Maximum Resistances[1]**
Applicable to FPGA I/O Banks

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. *These maximum values are provided for information only. Minimum output buffer resistance values depend on VCCxxxxIOBx, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website (also generated by the SoC Products Group Libero SoC toolset).*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)} = (V_{OLspec}) / I_{OLspec}$
3. $R_{(PULL\text{-}UP\text{-}MAX)} = (V_{CCImax} - V_{OHspec}) / I_{OHspec}$

Timing Characteristics

Table 2-38 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 3.0 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.60	7.20	0.04	0.97	0.39	7.34	6.18	2.52	2.46	9.39	8.23	ns
	–1	0.50	6.00	0.03	0.81	0.32	6.11	5.15	2.10	2.05	7.83	6.86	ns
8 mA	Std.	0.60	4.64	0.04	0.97	0.39	4.73	3.84	2.85	3.02	6.79	5.90	ns
	–1	0.50	3.87	0.03	0.81	0.32	3.94	3.20	2.37	2.52	5.65	4.91	ns
12 mA	Std.	0.60	3.37	0.04	0.97	0.39	3.43	2.67	3.07	3.39	5.49	4.73	ns
	–1	0.50	2.81	0.03	0.81	0.32	2.86	2.23	2.55	2.82	4.58	3.94	ns
16 mA	Std.	0.60	3.18	0.04	0.97	0.39	3.24	2.43	3.11	3.48	5.30	4.49	ns
	–1	0.50	2.65	0.03	0.81	0.32	2.70	2.03	2.59	2.90	4.42	3.74	ns
24 mA	Std.	0.60	2.93	0.04	0.97	0.39	2.99	2.03	3.17	3.83	5.05	4.09	ns
	–1	0.50	2.45	0.03	0.81	0.32	2.49	1.69	2.64	3.19	4.21	3.41	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

Table 2-39 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 3.0 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.60	9.75	0.04	0.97	0.39	9.93	8.22	2.52	2.31	11.99	10.28	ns
	–1	0.50	8.12	0.03	0.81	0.32	8.27	6.85	2.10	1.93	9.99	8.57	ns
8 mA	Std.	0.60	6.96	0.04	0.97	0.39	7.09	5.85	2.84	2.87	9.15	7.91	ns
	–1	0.50	5.80	0.03	0.81	0.32	5.91	4.88	2.37	2.39	7.62	6.59	ns
12 mA	Std.	0.60	5.35	0.04	0.97	0.39	5.45	4.58	3.06	3.23	7.51	6.64	ns
	–1	0.50	4.46	0.03	0.81	0.32	4.54	3.82	2.55	2.69	6.26	5.53	ns
16 mA	Std.	0.60	5.01	0.04	0.97	0.39	5.10	4.30	3.11	3.32	7.16	6.36	ns
	–1	0.50	4.17	0.03	0.81	0.32	4.25	3.58	2.59	2.77	5.97	5.30	ns
24 mA	Std.	0.60	4.67	0.04	0.97	0.39	4.75	4.28	3.16	3.66	6.81	6.34	ns
	–1	0.50	3.89	0.03	0.81	0.32	3.96	3.57	2.64	3.05	5.68	5.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Table 2-40 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCxxxxIOBx = 3.0 V
Applicable to MSS I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
8 mA	Std.	0.22	2.31	0.09	0.94	1.30	0.22	2.35	1.86	2.20	2.45	ns
	–1	0.18	1.92	0.07	0.78	1.09	0.18	1.96	1.55	1.83	2.04	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*

Table 2-63 • LVDS Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Typ.	Max.	Units
VCCFPGAIOBx	Supply voltage	2.375	2.5	2.625	V
VOL	Output low voltage	0.9	1.075	1.25	V
VOH	Output high voltage	1.25	1.425	1.6	V
I_{OL}[1]	Output lower current	0.65	0.91	1.16	mA
I_{OH}[1]	Output high current	0.65	0.91	1.16	mA
VI	Input voltage	0		2.925	V
I_{IH}[2]	Input high leakage current			15	µA
I_{IL}[2]	Input low leakage current			15	µA
V_{ODIFF}	Differential output voltage	250	350	450	mV
V_{OCM}	Output common mode voltage	1.125	1.25	1.375	V
V_{ICM}	Input common mode voltage	0.05	1.25	2.35	V
V_{IDIFF}	Input differential voltage	100	350		mV

Notes:

1. *I_{OL}/I_{OH} defined by V_{ODIFF}/(resistor network).*
2. *Currents are measured at 85°C junction temperature.*

Table 2-64 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	V_{REF} (typ.) (V)
1.075	1.325	Cross point	–

* *Measuring point = V_{trip}. See Table 2-22 on page 2-24 for a complete table of trip points.*

Timing Characteristics

Table 2-65 • LVDS
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCFPGAIOBx = 2.3 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.60	1.83	0.04	1.87	ns
–1	0.50	1.53	0.03	1.55	ns

Notes:

1. *For the derating values at specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*
2. *The above mentioned timing parameters correspond to 24mA drive strength.*

Table 2-66 • Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCFPGAIOBx	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-67 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	V_{REF} (typ.) (V)
1.64	1.94	Cross point	–

* *Measuring point = V_{trip}. See Table 2-22 on page 2-24 for a complete table of trip points.*

Timing Characteristics

Table 2-68 • LVPECL
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCFPGAIOBx = 3.0 V
Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.60	1.76	0.04	1.76	ns
–1	0.50	1.46	0.03	1.46	ns

Notes:

1. *For the derating values at specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.*
2. *The above mentioned timing parameters correspond to 24mA drive strength.*

Output Register

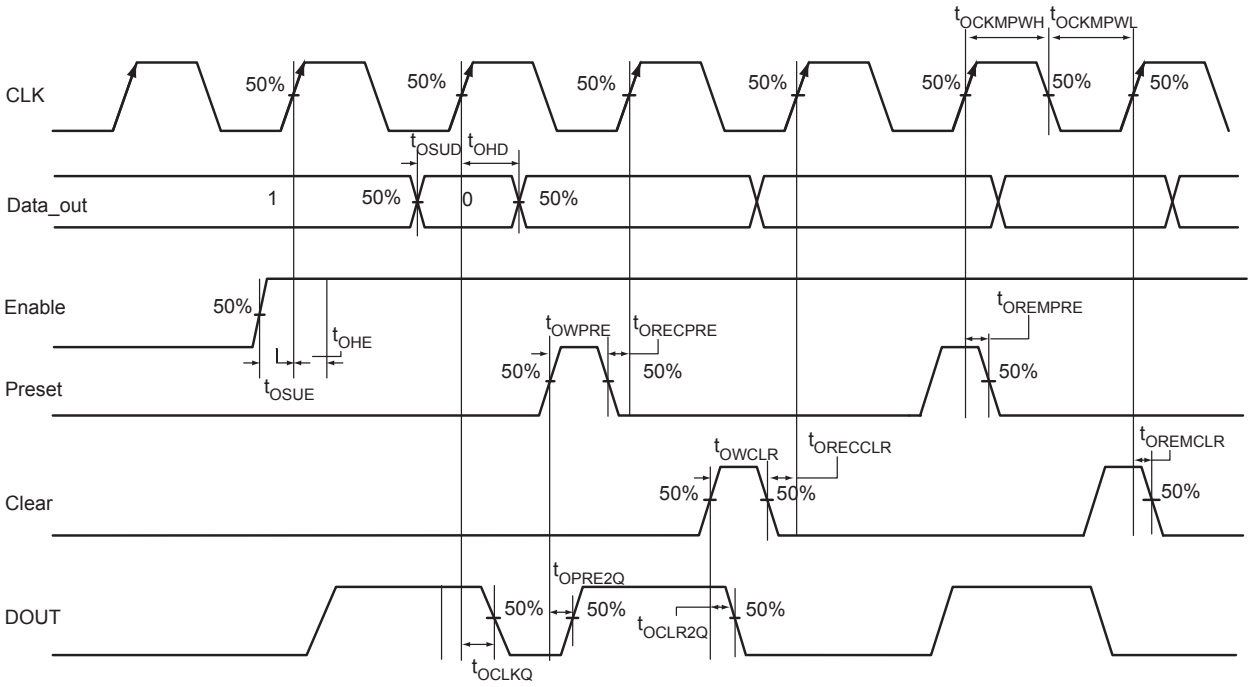

Figure 2-17 • **Output Register Timing Diagram**

Timing Characteristics

Table 2-72 • **Output Data Register Propagation Delays**
Worst Commercial-Case Conditions: T_J = 85°C, Worst-Case VCC = 1.425 V

Parameter	Description	–1	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.60	0.72	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.32	0.38	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	0.00	ns
t_{OSUE}	Enable Setup Time for the Output Data Register	0.44	0.53	ns
t_{OHE}	Enable Hold Time for the Output Data Register	0.00	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.82	0.98	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.82	0.98	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.23	0.27	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.23	0.27	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.22	0.22	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.22	0.22	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.36	0.36	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.32	0.32	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

Clock Conditioning Circuits

CCC Electrical Specifications

Timing Characteristics

***Table 2-86* • SmartFusion CCC/PLL Specification**

Parameter	Minimum	Typical	Maximum	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		350	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		350[1]	MHz
Delay Increments in Programmable Delay Blocks[2,3,4]		160		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Input Period Jitter			1.5	ns
Acquisition Time				
LockControl = 0			300	µs
LockControl = 1			6.0	ms
Tracking Jitter[5]				
LockControl = 0			1.6	ns
LockControl = 1			0.8	ns
Output Duty Cycle	48.5		5.15	%
Delay Range in Block: Programmable Delay 1[2,3]	0.6		5.56	ns
Delay Range in Block: Programmable Delay 2[2,3]	0.025		5.56	ns
Delay Range in Block: Fixed Delay[2,3]		2.2		ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT} [6,7]	Maximum Peak-to-Peak Period Jitter			

	SSO ≤ 2		SSO ≤ 4		SSO ≤ 8		SSO ≤ 16	
	FG/CS	PQ	FG/CS	PQ	FG/CS	PQ	FG/CS	PQ
0.75 MHz to 50 MHz	0.5%	1.6%	0.9%	1.6%	0.9%	1.6%	0.9%	1.8%
50 MHz to 250 MHz	1.75%	3.5%	9.3%	9.3%	9.3%	17.9%	10.0%	17.9%
250 MHz to 350 MHz	2.5%	5.2%	13.0%	13.0%	13.0%	25.0%	14.0%	25.0%

Notes:

1. *One of the CCC outputs (GLA0) is used as an MSS clock and is limited to 100 MHz (maximum) by software. Details regarding CCC/PLL are in the "PLLs, Clock Conditioning Circuitry, and On-Chip Crystal Oscillators" chapter of the SmartFusion Microcontroller Subsystem User's Guide.*
2. *This delay is a function of voltage and temperature. See Table 2-7 on page 2-9 for deratings.*
3. *T_J = 25°C, VCC = 1.5 V*
4. *When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help associated with the core for more information.*
5. *Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.*
6. *Measurement done with LVTTL 3.3 V 12 mA I/O drive strength and High slew rate. VCC/VCCPLL = 1.425 V, VCCI = 3.3V, 20 pF output load. All I/Os are placed outside of the PLL bank.*
7. *SSOs are outputs that are synchronous to a single clock domain and have their clock-to-out within ± 200 ps of each other.*
8. *VCO output jitter is calculated as a percentage of the VCO frequency. The jitter (in ps) can be calculated by multiplying the VCO period by the % jitter. The VCO jitter (in ps) applies to CCC_OUT regardless of the output divider settings. For example, if the jitter on VCO is 300 ps, the jitter on CCC_OUT is also 300 ps.*

FIFO

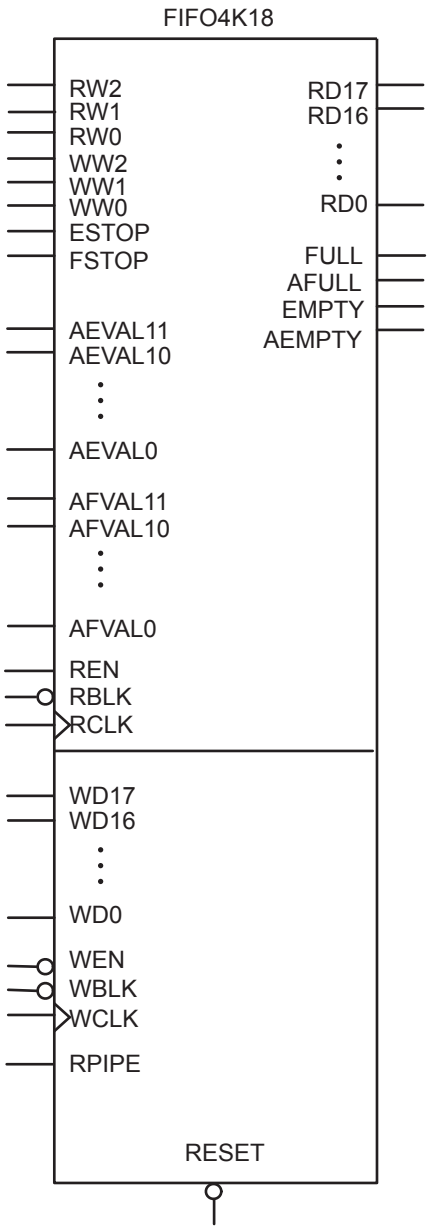

Figure 2-35 • **FIFO Model**

- Flash File System (RL-Flash) allows your embedded applications to create, save, read, and modify files in standard storage devices such as ROM, RAM, or FlashROM, using a standard serial peripheral interface (SPI). Many ARM-based microcontrollers have a practical requirement for a standard file system. With RL-FlashFS you can implement new features in embedded applications such as data logging, storing program state during standby modes, or storing firmware upgrades.

Micrium, in addition to µC/OS-III®, offers the following support for SmartFusion cSoC:

- µC/TCP-IP™ is a compact, reliable, and high-performance stack built from the ground up by Micrium and has the quality, scalability, and reliability that translates into a rapid configuration of network options, remarkable ease-of-use, and rapid time-to-market.
- µC/Probe™ is one of the most useful tools in embedded systems design and puts you in the driver's seat, allowing you to take charge of virtually any variable, memory location, and I/O port in your embedded product, while your system is running.

References

PCB Files

A2F500 SmartFusion Development Kit PCB Files

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=130770

A2F200 SmartFusion Development Kit PCB Files

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=130773

Application Notes

SmartFusion cSoC Board Design Guidelines

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129815

Re-Programming the eNVM Blocks Using the Cortex-M3

In this mode the Cortex-M3 is executing the eNVM programming algorithm from eSRAM. Since individual pages (132 bytes) of the eNVM can be write-protected, the programming algorithm software can be protected from inadvertent erasure. When reprogramming the eNVM, both MSS I/Os and FPGA I/Os are available as interfaces for sourcing the new eNVM image. The SoC Products Group provides working example projects for SoftConsole, IAR, and Keil development environments. These can be downloaded via the SoC Products Group Firmware Catalog.

Alternately, the eNVM can be reprogrammed by the Cortex-M3 via the IAP driver. This is necessary when using an encrypted image.

Secure Programming

For background, refer to the "Security in Low Power Flash Devices" chapter of the *Fusion FPGA Fabric User's Guide* on the SoC Products Group website. SmartFusion ISP behaves identically to Fusion ISP. IAP of SmartFusion cSoCs is accomplished by using the IAP driver. Only the FPGA fabric and the eNVM can be reprogrammed with the protection of security measures by using the IAP driver.

Typical Programming and Erase Times

Table 4-3 documents the typical programming and erase times for two components of SmartFusion cSoCs, FPGA fabric and eNVM, using the SoC Products Group's FlashPro hardware and software. These times will be different for other ISP and IAP methods. The **Program** action in FlashPro software includes erase, program, and verify to complete.

The typical programming (including erase) time per page of the eNVM is 8 ms.

***Table 4-3* • Typical Programming and Erase Times**

	FPGA Fabric (seconds)			eNVM (seconds)			FlashROM (seconds)		
	A2F060	**A2F200**	**A2F500**	**A2F060**	**A2F200**	**A2F500**	**A2F060**	**A2F200**	**A2F500**
Erase	21	21	21	N/A	N/A	N/A	21	21	21
Program	28	35	48	18	39	71	22	22	22
Verify	2	6	12	9	18	37	1	1	1

References

User's Guides

DirectC User's Guide

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=132588

In-System Programming (ISP) of Microsemi's Low-Power Flash Devices Using FlashPro4/3/3X

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129973

Programming Flash Devices HandBook

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129930

Application Notes on IAP Programming Technique

SmartFusion cSoC: Programming FPGA Fabric and eNVM Using In-Application Programming Interface App Note

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129818

SmartFusion cSoC: Basic Bootloader and Field Upgrade eNVM Through IAP Interface App Note

http://www.microsemi.com/index.php?option=com_docman&task=doc_download&gid=129823

Pin No.	CS288		
	A2F060 Function	A2F200 Function	A2F500 Function
C21	IO17NDB0V0	GBA2/IO20PDB1V0	GBA2/IO27PDB1V0
D1	EMC_DB[14]/IO45NDB5V0	EMC_DB[14]/GAB2/IO71NDB5V0	EMC_DB[14]/GAB2/IO88NDB5V0
D3	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
D19	GND	GND	GND
D21	VCCFPGAIOB1	VCCFPGAIOB1	VCCFPGAIOB1
E1	EMC_DB[13]/IO44PDB5V0	EMC_DB[13]/GAC2/IO70PDB5V0	EMC_DB[13]/GAC2/IO87PDB5V0
E3	EMC_DB[12]/IO44NDB5V0	EMC_DB[12]/IO70NDB5V0	EMC_DB[12]/IO87NDB5V0
E5	GNDQ	GNDQ	GNDQ
E6	EMC_BYTEN[0]/IO02NDB0V0	EMC_BYTEN[0]/GAC0/IO02NDB0V0	EMC_BYTEN[0]/GAC0/IO07NDB0V0
E7	EMC_BYTEN[1]/IO02PDB0V0	EMC_BYTEN[1]/GAC1/IO02PDB0V0	EMC_BYTEN[1]/GAC1/IO07PDB0V0
E8	EMC_OEN1_N/IO03PDB0V0	EMC_OEN1_N/IO03PDB0V0	EMC_OEN1_N/IO08PDB0V0
E9	EMC_AB[3]/IO05PDB0V0	EMC_AB[3]/IO05PDB0V0	EMC_AB[3]/IO09PDB0V0
E10	EMC_AB[10]/IO09NDB0V0	EMC_AB[10]/IO09NDB0V0	EMC_AB[10]/IO11NDB0V0
E11	EMC_AB[7]/IO07PDB0V0	EMC_AB[7]/IO07PDB0V0	EMC_AB[7]/IO12PDB0V0
E12	EMC_AB[13]/IO10PDB0V0	EMC_AB[13]/IO10PDB0V0	EMC_AB[13]/IO14PDB0V0
E13	EMC_AB[16]/IO12NDB0V0	EMC_AB[16]/IO12NDB0V0	EMC_AB[16]/IO17NDB0V0
E14	EMC_AB[17]/IO12PDB0V0	EMC_AB[17]/IO12PDB0V0	EMC_AB[17]/IO17PDB0V0
E15	GCC0/IO18NPB0V0	GCB0/IO27NDB1V0	GCB0/IO34NDB1V0
E16	GCA1/IO20PPB0V0	GCB1/IO27PDB1V0	GCB1/IO34PDB1V0
E17	GCC1/IO18PPB0V0	GCB2/IO24PDB1V0	GCB2/IO33PDB1V0
E19	GCB2/IO22PPB1V0	GCA0/IO28NDB1V0	GCA0/IO36NDB1V0 *
E21	IO21NDB1V0	GCA1/IO28PDB1V0	GCA1/IO36PDB1V0 *
F1	VCCFPGAIOB5	VCCFPGAIOB5	VCCFPGAIOB5
F3	GFB2/IO42NDB5V0	GFB2/IO68NDB5V0	GFB2/IO85NDB5V0
F5	GFA2/IO42PDB5V0	GFA2/IO68PDB5V0	GFA2/IO85PDB5V0
F6	EMC_DB[11]/IO43PDB5V0	EMC_DB[11]/IO69PDB5V0	EMC_DB[11]/IO86PDB5V0
F7	GND	GND	GND
F8	NC	GFC1/IO66PPB5V0	GFC1/IO83PPB5V0
F9	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0
F10	EMC_AB[11]/IO09PDB0V0	EMC_AB[11]/IO09PDB0V0	EMC_AB[11]/IO11PDB0V0
F11	EMC_AB[6]/IO07NDB0V0	EMC_AB[6]/IO07NDB0V0	EMC_AB[6]/IO12NDB0V0

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	CS288		
	A2F060 Function	A2F200 Function	A2F500 Function
W14	ADC5	CM2	CM2
W15	NC	ABPS5	ABPS5
W16	GNDAQ	GNDAQ	GNDAQ
W17	NC	VCC33SDD1	VCC33SDD1
W18	NC	GNDSDD1	GNDSDD1
W19	PTBASE	PTBASE	PTBASE
W21	SPI_0_DI/GPIO_17	SPI_0_DI/GPIO_17	SPI_0_DI/GPIO_17
Y1	VCC33AP	VCC33AP	VCC33AP
Y21	SPI_0_DO/GPIO_16	SPI_0_DO/GPIO_16	SPI_0_DO/GPIO_16

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin No.	FG256		
	A2F060 Function	A2F200 Function	A2F500 Function
P10	TM0	TM3	TM3
P11	GNDA	GNDA	GNDA
P12	VCCMAINXTAL	VCCMAINXTAL	VCCMAINXTAL
P13	GNDLPXTAL	GNDLPXTAL	GNDLPXTAL
P14	VDDBAT	VDDBAT	VDDBAT
P15	PTEM	PTEM	PTEM
P16	PTBASE	PTBASE	PTBASE
R1	PCAP	PCAP	PCAP
R2	SDD0	SDD0	SDD0
R3	ADC0	ABPS0	ABPS0
R4	ADC3	TM0	TM0
R5	NC	ABPS2	ABPS2
R6	NC	ADC1	ADC1
R7	NC	VCC33ADC0	VCC33ADC0
R8	VCC15ADC0	VCC15ADC1	VCC15ADC1
R9	ADC10	ADC7	ADC7
R10	ABPS1	ABPS7	ABPS7
R11	NC	ABPS4	ABPS4
R12	MAINXIN	MAINXIN	MAINXIN
R13	MAINXOUT	MAINXOUT	MAINXOUT
R14	LPXIN	LPXIN	LPXIN
R15	LPXOUT	LPXOUT	LPXOUT
R16	VCC33A	VCC33A	VCC33A
T1	NCAP	NCAP	NCAP
T2	ADC1	ABPS1	ABPS1
T3	ADC2	CM0	CM0
T4	NC	GNDTM0	GNDTM0
T5	NC	ADC0	ADC0
T6	NC	VAREF0	VAREF0
T7	NC	GND33ADC0	GND33ADC0
T8	GND15ADC0	GND15ADC1	GND15ADC1

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin Number	FG484	
	A2F200 Function	A2F500 Function
AA13	NC	ADC10
AA14	NC	ADC9
AA15	NC	GND15ADC2
AA16	MAINXIN	MAINXIN
AA17	MAINXOUT	MAINXOUT
AA18	LPXIN	LPXIN
AA19	LPXOUT	LPXOUT
AA20	NC	NC
AA21	NC	NC
AA22	SPI_1_CLK/GPIO_26	SPI_1_CLK/GPIO_26
AB1	GND	GND
AB2	GPIO_13/IO36RSB4V0	GPIO_13/IO45RSB4V0
AB3	GPIO_14/IO35RSB4V0	GPIO_14/IO44RSB4V0
AB4	GND	GND
AB5	PCAP	PCAP
AB6	NCAP	NCAP
AB7	ABPS3	ABPS3
AB8	ADC3	ADC3
AB9	GND15ADC0	GND15ADC0
AB10	VCC33ADC1	VCC33ADC1
AB11	VAREF1	VAREF1
AB12	TM2	TM2
AB13	CM2	CM2
AB14	ABPS4	ABPS4
AB15	GNDAQ	GNDAQ
AB16	GNDMAINXTAL	GNDMAINXTAL
AB17	GNDLPXTAL	GNDLPXTAL
AB18	VCCLPXTAL	VCCLPXTAL
AB19	VDDBAT	VDDBAT
AB20	PTBASE	PTBASE
AB21	NC	NC
AB22	GND	GND
B1	EMC_DB[15]/GAA2/IO71PDB5V0	EMC_DB[15]/GAA2/IO88PDB5V0
B2	GND	GND

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin Number	FG484	
	A2F200 Function	A2F500 Function
C15	EMC_AB[17]/IO12PDB0V0	EMC_AB[17]/IO17PDB0V0
C16	EMC_AB[24]/IO16NDB0V0	EMC_AB[24]/IO20NDB0V0
C17	EMC_AB[22]/IO15NDB0V0	EMC_AB[22]/IO19NDB0V0
C18	EMC_AB[23]/IO15PDB0V0	EMC_AB[23]/IO19PDB0V0
C19	GBA0/IO19NPB0V0	GBA0/IO23NPB0V0
C20	NC	NC
C21	GBC2/IO21PDB1V0	GBC2/IO30PDB1V0
C22	GBB2/IO20NDB1V0	GBB2/IO27NDB1V0
D1	GND	GND
D2	EMC_DB[12]/IO70NDB5V0	EMC_DB[12]/IO87NDB5V0
D3	EMC_DB[13]/GAC2/IO70PDB5V0	EMC_DB[13]/GAC2/IO87PDB5V0
D4	NC	NC
D5	NC	NC
D6	GND	GND
D7	NC	IO00NPB0V0
D8	NC	IO03NPB0V0
D9	GND	GND
D10	EMC_OEN0_N/IO03NDB0V0	EMC_OEN0_N/IO08NDB0V0
D11	EMC_AB[10]/IO09NDB0V0	EMC_AB[10]/IO11NDB0V0
D12	EMC_AB[11]/IO09PDB0V0	EMC_AB[11]/IO11PDB0V0
D13	EMC_AB[9]/IO08PDB0V0	EMC_AB[9]/IO13PDB0V0
D14	GND	GND
D15	GBC1/IO17PPB0V0	GBC1/IO22PPB0V0
D16	EMC_AB[25]/IO16PDB0V0	EMC_AB[25]/IO20PDB0V0
D17	GND	GND
D18	GBA1/IO19PPB0V0	GBA1/IO23PPB0V0
D19	NC	NC
D20	NC	NC
D21	IO21NDB1V0	IO30NDB1V0
D22	GND	GND
E1	GFC2/IO67PPB5V0	GFC2/IO84PPB5V0
E2	VCCFPGAIOB5	VCCFPGAIOB5
E3	GFA2/IO68PDB5V0	GFA2/IO85PDB5V0
E4	GND	GND

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Pin Number	FG484	
	A2F200 Function	A2F500 Function
E5	NC	NC
E6	GNDQ	GNDQ
E7	VCCFPGAIOB0	VCCFPGAIOB0
E8	NC	IO00PPB0V0
E9	NC	NC
E10	VCCFPGAIOB0	VCCFPGAIOB0
E11	EMC_AB[4]/IO06NDB0V0	EMC_AB[4]/IO10NDB0V0
E12	EMC_AB[5]/IO06PDB0V0	EMC_AB[5]/IO10PDB0V0
E13	VCCFPGAIOB0	VCCFPGAIOB0
E14	GBC0/IO17NPB0V0	GBC0/IO22NPB0V0
E15	NC	NC
E16	VCCFPGAIOB0	VCCFPGAIOB0
E17	NC	VCOMPLA1
E18	NC	IO25NPB1V0
E19	GND	GND
E20	NC	NC
E21	VCCFPGAIOB1	VCCFPGAIOB1
E22	IO22NDB1V0	IO32NDB1V0
F1	GFB1/IO65PPB5V0	GFB1/IO82PPB5V0
F2	IO67NPB5V0	IO84NPB5V0
F3	GFB2/IO68NDB5V0	GFB2/IO85NDB5V0
F4	EMC_DB[10]/IO69NPB5V0	EMC_DB[10]/IO86NPB5V0
F5	VCCFPGAIOB5	VCCFPGAIOB5
F6	VCCPLL	VCCPLL0
F7	VCOMPLA	VCOMPLA0
F8	NC	NC
F9	NC	NC
F10	NC	NC
F11	NC	NC
F12	NC	NC
F13	EMC_AB[20]/IO14NDB0V0	EMC_AB[20]/IO21NDB0V0
F14	EMC_AB[21]/IO14PDB0V0	EMC_AB[21]/IO21PDB0V0
F15	GNDQ	GNDQ
F16	NC	VCCPLL1

Notes:

1. *Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.*
2. **: Indicates that the signal assigned to the pins as a CLKBUF/CLKBUF_LVPECL/CLKBUF_LVDS goes through a glitchless mux. In order for the glitchless mux to operate correctly, the signal must be a free-running clock signal. Refer to the 'Glitchless MUX' section in the SmartFusion Microcontroller Subsystem User's Guide for more details.*

Revision	Changes	Page
	The A2F060 device was added to product information tables.	N/A
	The "Product Ordering Codes" table was updated to removed Std. speed and add speed grade 1. Pre-production was removed from the application ordering code category.	VI
	The "SmartFusion cSoC Block Diagram" was revised.	IV
	The "Datasheet Categories" section was updated, referencing the "SmartFusion cSoC Block Diagram" table, which is new.	1-4, IV
	The "VCCI" parameter was renamed to "VCCxxxxIOBx." "Advanced I/Os" were renamed to "FPGA I/Os." Generic pin names that represent multiple pins were standardized with a lower case x as a placeholder. For example, VAREFx designates VAREF0, VAREF1, and VAREF2. Modes were renamed as follows: Operating mode was renamed to SoC mode. 32KHz Active mode was renamed to Standby mode. Battery mode was renamed to Time Keeping mode. Table entries have been filled with values as data has become available.	N/A
	Table 2-1 • Absolute Maximum Ratings, Table 2-2 • Analog Maximum Ratings, and Table 2-3 • Recommended Operating Conditions[5,6] were revised extensively.	2-1 through 2-3
	Device names were updated in Table 2-6 • Package Thermal Resistance.	2-7
	Table 2-8 • Power Supplies Configuration was revised extensively.	2-10
	Table 2-11 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings was revised extensively.	2-11
	Removed "Example of Power Calculation."	N/A
	Table 2-14 • Different Components Contributing to Dynamic Power Consumption in SmartFusion cSoCs was revised extensively.	2-12
	Table 2-15 • Different Components Contributing to the Static Power Consumption in SmartFusion cSoCs was revised extensively.	2-13
	The "Power Calculation Methodology" section was revised.	2-14
	Table 2-83 • Electrical Characteristics of the RC Oscillator was revised extensively.	2-61
	Table 2-85 • Electrical Characteristics of the Low Power Oscillator was revised extensively.	2-62
	The parameter t_{RSTBQ} was changed to T_{C2CWRH} in Table 2-87 • RAM4K9.	2-69
	The 12-bit mode row for integral non-linearity was removed from Table 2-95 • ADC Specifications. The typical value for 10-bit mode was revised. The table note was punctuated correctly to make it clear.	2-81
	Figure 37-34 • Write Access after Write onto Same Address, Figure 37-34 • Read Access after Write onto Same Address, and Figure 37-34 • Write Access after Read onto Same Address were deleted.	N/A
	Table 2-99 • Voltage Regulator was revised extensively.	2-87
	The "Serial Peripheral Interface (SPI) Characteristics" section and "Inter-Integrated Circuit (I^2C) Characteristics" section are new.	2-89, 2-91

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